General purpose transistor (isolated transistor and diode)

US5L12

A 2SD2675 and a RB461F are housed independently in a TUMT5 package.

Applications

DC / DC converter Motor driver

● Features

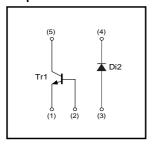
1) Tr : Low Vce(sat) Di : Low VF

2) Small package

●Structure

Silicon epitaxial planar transistor Schottky barrier diode

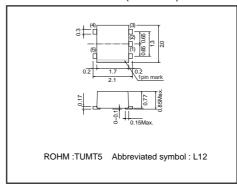
●Equivalent circuit



Packaging specifications

Туре	US5L12
Package	TUMT5
Marking	L12
Code	TR
Basic ordering unit(pieces)	3000

●External dimensions (Unit : mm)



ROHM

Rev.A

●Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	30	V
Collector-emitter voltage	Vceo	30	V
Emitter-base voltage	Vево	6	V
Collector current	Ic	1	Α
	Іср	2	A *1
Power dissipation	Pc	0.7	W/ELEMENT *2
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	-40 to +125	°C

Di2

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	25	V
Reverse voltage (DC)	VR	20	V
Average rectified forward current	lF	700	mA
Forward current surge peak (60Hz, 1∞)	IFSM	3	Α
Power dissipation	Po	0.5	W/ELEMENT *
Junction temperature	Tj	125	°C
Range of storage temperature	Tstg	-40 to +125	°C

^{*} Mounted on a 25mm×25mm×^t 0.8mm ceramic substrate

Tr1& Di2

Parameter	Symbol	Limits	Unit
Total power dissipation	PD	0.4	W/TOTAL *1
Total power dissipation		1.0	W/TOTAL *2

^{*1} Each terminal mounted on a recommended land *2 Mounted on a 25mm×25mm×^t0.8mm ceramic substrate

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	30	_	_	V	Ic=10μA
Collector-emitter breakdown voltage	BVceo	30	_	_	V	Ic=1mA
Emitter-base breakdown voltage	ВУЕВО	6	_	_	V	Iε=10μA
Collector cutoff current	Ісво	_	_	100	nA	Vcb=30V
Emitter cutoff current	ІЕВО	_	_	100	nA	V _{EB} =6V
Collector-emitter saturation voltage	VCE(sat)	_	120	350	mV	Ic=500mA, Iв=25mA
DC current gain	hfe	270	_	680	_	Vce=2V, Ic=100mA *
Transition frequency	f⊤	_	320	_	MHz	Vce=2V, Ie=100mA, f=100MHz *
Collector output capacitance	Cob	_	7	_	pF	Vcb=10V, Ie=0A, f=1MHz
* Pulsed						

Di2

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	VF	_	450	490	mV	I=700mA
Reverse current	lR	_	_	200	μΑ	V _R =20V
Reverse recovery time	trr	_	9	_	ns	IF=IR=100mA, Irr=0.1IR



^{*1} Single pulse, Pw=1ms. *2 Mounted on a 25mm×25mm×¹0.8mm ceramic substrate

•Electrical characteristic curves

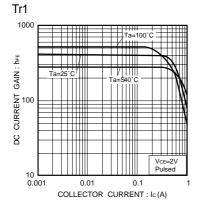


Fig.1 DC current gain vs. collector current

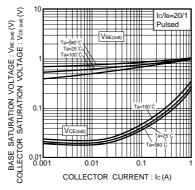


Fig.2 Collector-emitter saturation voltage base-emitter saturation voltage vs. collector current

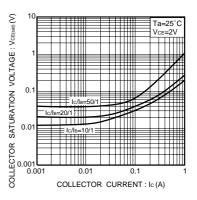


Fig.3 Collector-emitter saturation voltage vs. collector current

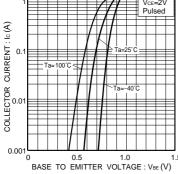


Fig.4 Grounded emitter propagation characteristics

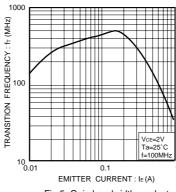


Fig.5 Gain bandwidth product vs. emitter current

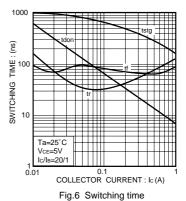
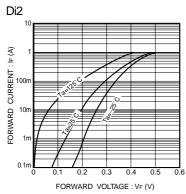


Fig.7 Collector output capacitance vs. collector-base voltage Emitter input capacitance vs. emitter-base voltage

Transistors



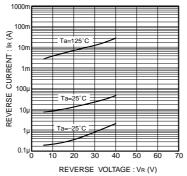


Fig.8 Forward characteristics

Fig.9 Reverse characteristics

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